

ABSTRACT OF THE DISCLOSURE

A liquid-phase growth process for continuously growing a crystal film on a plurality of substrates with respect to their one side surfaces, characterized in that  
5 said plurality of substrates are kept afloat on the surface of a flowing solution for liquid-phase epitaxy which comprises a crystallizing material dissolved in a solvent in a supersaturated state and which is flowing in a solution flow passage, and while said plurality of  
10 substrates being moved by virtue of said flowing solution in said solution flow passage, a crystal film is grown on the surfaces of said plurality of substrates which are in contact with said flowing solution. A liquid-phase growth apparatus suitable for  
15 practicing said liquid-phase growth process.